Product data sheet

1. General description

The 74LV132 is a low-voltage Si-gate CMOS device that is pin and function compatible with 74HC132 and 74HCT132.

The 74LV132 contains four 2-input NAND gates which accept standard input signals. They are capable of transforming slowly changing input signals into sharply defined, jitter-free output signals.

The gate switches at different points for positive and negative-going signals. The difference between the positive voltage V_{T+} and the negative voltage V_{T-} is defined as the input hysteresis voltage V_{H} .

2. Features and benefits

- Wide operating voltage: 1.0 V to 5.5 V
- Optimized for low voltage applications: 1.0 V to 3.6 V
- Accepts TTL input levels between $V_{CC} = 2.7$ V and $V_{CC} = 3.6$ V
- Typical output ground bounce < 0.8 V at V_{CC} = 3.3 V and T_{amb} = 25 °C
- Typical HIGH-level output voltage (V_{OH}) undershoot: > 2 V at V_{CC} = 3.3 V and T_{amb} = 25 °C
- ESD protection:
 - HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from –40 °C to +85 °C and from –40 °C to +125 °C

3. Applications

- Wave and pulse shapers for highly noisy environments
- Astable multivibrators
- Monostable multivibrators

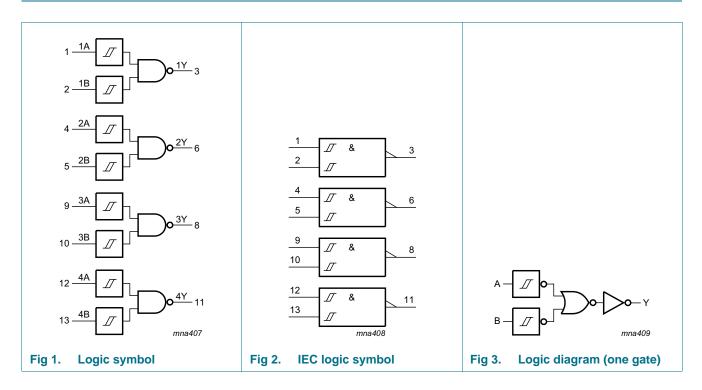


4. Ordering information

Table 1. Ordering information

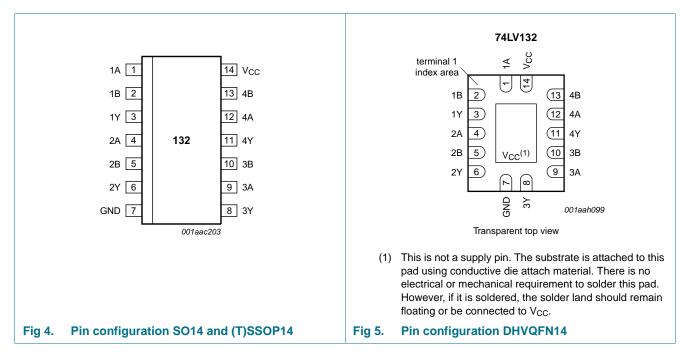
Type number	Package								
	Temperature range	Name	Description	Version					
74LV132D	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1					
74LV132DB	–40 °C to +125 °C	SSOP14	plastic shrink small outline package; 14 leads; body width 5.3 mm	SOT337-1					
74LV132PW	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1					
74LV132BQ	–40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body $2.5 \times 3 \times 0.85$ mm	SOT762-1					

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 2. **Pin description** Symbol Pin Description 1A to 4A 1, 4, 9, 12 data input 1B to 4B 2, 5, 10, 13 data input 1Y to 4Y 3, 6, 8, 11 data output GND 7 ground (0 V) Vcc 14 supply voltage

7. Functional description

Table 3. Function table

H = HIGH voltage level; L = LOW voltage level.

Input	Output	
nA	nB	nY
L	L	Н
L	Н	Н
н	L	Н
Н	Н	L

8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CC}	supply voltage			-0.5	+7.0	V
I _{IK}	input clamping current	V_{I} < -0.5 V or V_{I} > V_{CC} + 0.5 V	<u>[1]</u>	-	±20	mA
I _{OK}	output clamping current	$V_{\rm O}$ < –0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V	<u>[1]</u>	-	±50	mA
lo	output current	$V_{O} = -0.5 \text{ V}$ to ($V_{CC} + 0.5 \text{ V}$)		-	±25	mA
I _{CC}	supply current			-	50	mA
I _{GND}	ground current			-50	-	mA
T _{stg}	storage temperature			-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to \ +125 \ ^{\circ}C$				
		SO14 package	[2]	-	500	mW
		(T)SSOP14 package	<u>[3]</u>	-	500	mW
		DHVQFN14 package	<u>[4]</u>	-	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] $~~P_{tot}$ derates linearly with 8 mW/K above 70 °C.

[3] P_{tot} derates linearly with 5.5 mW/K above 60 °C.

[4] P_{tot} derates linearly with 4.5 mW/K above 60 °C.

9. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CC}	supply voltage ^[1]		1.0	3.3	5.5	V
VI	input voltage		0	-	V _{CC}	V
Vo	output voltage		0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	°C

[1] The static characteristics are guaranteed from V_{CC} = 1.2 V to V_{CC} = 5.5 V, but LV devices are guaranteed to function down to V_{CC} = 1.0 V (with input levels GND or V_{CC}).

10. Static characteristics

Table 6.Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40	°C to +8	5 °C	–40 °C to	Unit	
			Min	Typ[1]	Max	Min	Max	-
V _{OH}	HIGH-level output voltage	$V_{I} = V_{T+} \text{ or } V_{T-}$						
		$I_0 = -100 \ \mu\text{A}; \ V_{CC} = 1.2 \ \text{V}$	-	1.2	-	-	-	V
		$I_{O} = -100 \ \mu\text{A}; \ V_{CC} = 2.0 \ \text{V}$	1.8	2.0	-	1.8	-	V
		$I_{O} = -100 \ \mu\text{A}; \ V_{CC} = 2.7 \ \text{V}$	2.5	2.7	-	2.5	-	V
		$I_{O} = -100 \ \mu\text{A}; \ V_{CC} = 3.0 \ \text{V}$	2.8	3.0	-	2.8	-	V
		$I_{O} = -100 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$	4.3	4.5	-	4.3	-	V
		$I_{O} = -6 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.4	2.82	-	2.2	-	V
		$I_{O} = -12 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.6	4.2	-	3.5	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{T+} \text{ or } V_{T-}$						
		$I_0 = 100 \ \mu A; \ V_{CC} = 1.2 \ V$	-	0	-	-	-	V
		$I_0 = 100 \ \mu A; \ V_{CC} = 2.0 \ V$	-	0	0.2	-	0.2	V
		$I_0 = 100 \ \mu\text{A}; \ V_{CC} = 2.7 \ \text{V}$	-	0	0.2	-	0.2	V
		$I_0 = 100 \ \mu\text{A}; \ V_{CC} = 3.0 \ \text{V}$	-	0	0.2	-	0.2	V
		$I_0 = 100 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$	-	0	0.2	-	0.2	V
		$I_0 = 6 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	0.25	0.40	-	0.50	V
		$I_0 = 12 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.35	0.55	-	0.65	V
lı	input leakage current	$V_1 = V_{CC} \text{ or GND};$ $V_{CC} = 5.5 \text{ V}$	-	-	1.0	-	1.0	μA
I _{CC}	supply current	$V_{I} = V_{CC} \text{ or GND}; I_{O} = 0 \text{ A};$ $V_{CC} = 5.5 \text{ V}$	-	-	20.0	-	40	μA
Δl _{CC}	additional supply current	per input; V _I = V _{CC} – 0.6 V; V _{CC} = 2.7 V to 3.6 V	-	-	500	-	850	μA
Cı	input capacitance		-	3.5	-	-	-	pF

[1] Typical values are measured at T_{amb} = 25 °C.

11. Dynamic characteristics

Table 7. Dynamic characteristics

GND = 0 V; For test circuit see Figure 7.

Symbol	Parameter	Conditions	ns -40 °C to +85 °C		°C	_40 °C t	Unit		
				Min	Typ[1]	Max	Min	Max	
t _{pd}	propagation delay	nA, nB to nY; see <u>Figure 6</u>	[2]						
		V _{CC} = 1.2 V		-	65	-	-	-	ns
		V _{CC} = 2.0 V		-	18	34	-	43	ns
		V _{CC} = 2.7 V		-	15	24	-	30	ns
		V_{CC} = 3.0 V to 3.6 V; C_L = 15 pF	<u>[3]</u>	-	10	-	-	-	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	<u>[3]</u>	-	12	20	-	25	ns
		$V_{CC} = 4.5 V \text{ to } 5.5 V$	<u>[3]</u>	-	9.0	14	-	17	ns
C _{PD}	power dissipation capacitance	$\label{eq:classical_linear} \begin{split} & C_L = 50 \text{ pF; } f_i = 1 \text{ MHz;} \\ & V_I = \text{GND to } V_{\text{CC}} \end{split}$	<u>[4]</u>	-	24	-	-	-	pF

[1] All typical values are measured at T_{amb} = 25 °C.

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

[3] Typical values are measured at nominal supply voltage (V_{CC} = 3.3 V and V_{CC} = 5.0 V).

[4] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 $\textbf{P}_{D} = \textbf{C}_{PD} \times \textbf{V}_{CC}{}^{2} \times \textbf{f}_{i} \times \textbf{N} + \boldsymbol{\Sigma}(\textbf{C}_{L} \times \textbf{V}_{CC}{}^{2} \times \textbf{f}_{o}) \text{ where:}$

 $f_i = \mbox{input}$ frequency in MHz, $f_o = \mbox{output}$ frequency in MHz

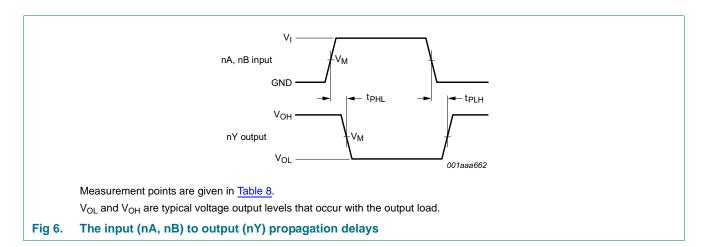
 C_L = output load capacitance in pF

 V_{CC} = supply voltage in V

N = number of inputs switching

 $\Sigma(C_L \times V_{CC}{}^2 \times f_o)$ = sum of the outputs.

12. Waveforms



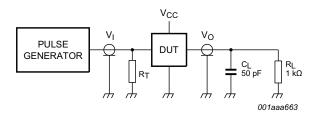
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Quad 2-input NAND Schmitt trigger

Table 0. Inclusionent points								
Supply voltage	Input	Output						
V _{cc}	V _M	V _M						
< 2.7 V	0.5V _{CC}	0.5V _{CC}						
2.7 V to 3.6 V	1.5 V	1.5 V						
≥ 4.5 V	0.5V _{CC}	0.5V _{CC}						





Test data is given in Table 9.

Definitions test circuit:

 R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

 R_L = Load resistance.

 C_L = Load capacitance including jig and probe capacitance.

Fig 7. Test circuit for measuring switching times

Table 9. Test data

Supply voltage	Input				
V _{cc}	V _I t _r , t _f				
< 2.7 V	V _{CC}	≤ 2.5 ns			
2.7 V to 3.6 V	2.7 V	≤ 2.5 ns			
≥ 4.5 V	V _{CC}	≤ 2.5 ns			

13. Transfer characteristics

Table 10. Transfer characteristics

GND = 0 V; For test circuit see <u>Figure 7</u>.

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ <mark>[1]</mark>	Max	Min	Max	
V _{T+}	positive-going	see Figure 6						
	threshold voltage	V _{CC} = 1.2 V	-	0.70	-	-	-	V
		V _{CC} = 2.0 V	0.8	1.10	1.4	0.8	1.4	V
		$V_{CC} = 2.7 V$	1.0	1.45	2.0	1.0	2.0	V
		V _{CC} = 3.0 V	1.2	1.60	2.2	1.2	2.2	V
		V _{CC} = 3.6 V	1.5	1.95	2.4	1.5	2.4	V
		V _{CC} = 4.5 V	1.7	2.50	3.2	1.7	3.2	V
		V _{CC} = 5.5 V	2.1	3.00	3.9	2.1	3.9	V

74LV132 Product data sheet

74LV132

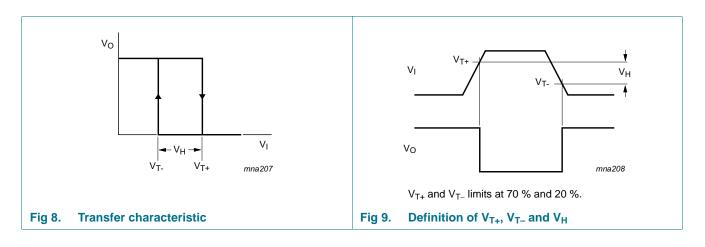
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Symbol	Parameter	Conditions	-40	–40 °C to +85 °C			o +125 °C	Unit
			Min	Typ[1]	Max	Min	Max	_
V _{T-}	negative-going	see <u>Figure 6</u>						
	threshold voltage	V _{CC} = 1.2 V	-	0.34	-	-	-	V
		V _{CC} = 2.0 V	0.3	0.65	0.9	0.3	0.9	V
		V _{CC} = 2.7 V	0.4	0.90	1.4	0.4	1.4	V
		V _{CC} = 3.0 V	0.6	1.05	1.5	0.6	1.5	V
		V _{CC} = 3.6 V	0.8	1.30	1.8	0.8	1.8	V
		V _{CC} = 4.5 V	0.9	1.60	2.0	0.9	2.0	V
		V _{CC} = 5.5 V	1.2	2.00	2.6	1.2	2.6	V
V _H	hysteresis voltage	$(V_{T+} - V_{T-})$; see Figure 6						
		V _{CC} = 1.2 V	-	0.3	-	-	-	V
		V _{CC} = 2.0 V	0.2	0.55	0.8	0.2	0.8	V
		V _{CC} = 2.7 V	0.3	0.60	1.1	0.3	1.1	V
		V _{CC} = 3.0 V	0.4	0.65	1.2	0.4	1.2	V
		V _{CC} = 3.6 V	0.4	0.70	1.2	0.4	1.2	V
		V _{CC} = 4.5 V	0.4	0.80	1.4	0.4	1.4	V
		V _{CC} = 5.5 V	0.6	1.00	1.5	0.6	1.5	V

Table 10.Transfer characteristics ... continuedGND = 0 V; For test circuit see Figure 7.

[1] All typical values are measured at $T_{amb} = 25 \text{ °C}$.

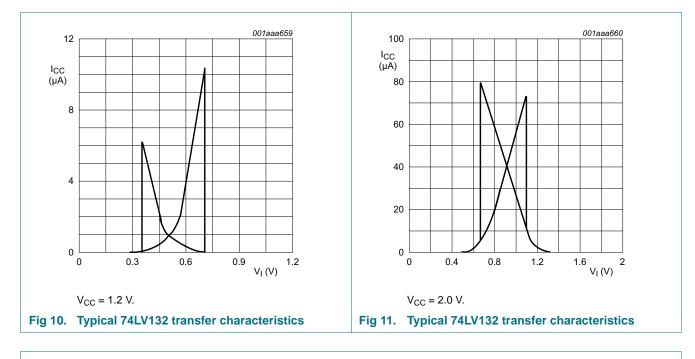
14. Waveforms transfer characteristics

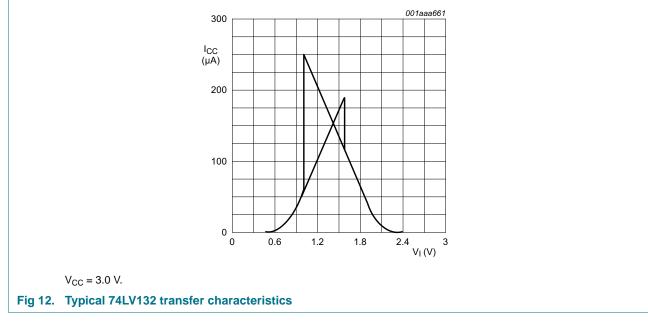


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15. Package outline

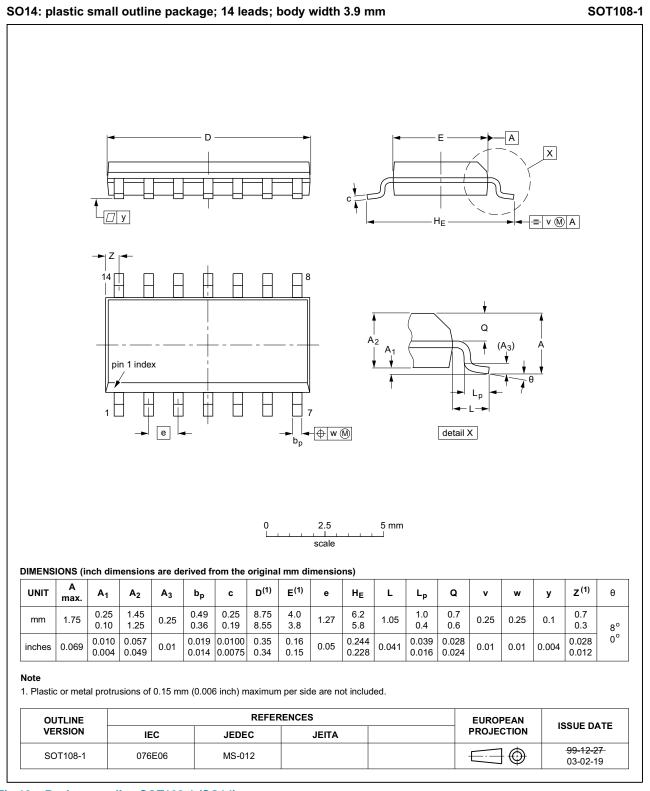


Fig 13. Package outline SOT108-1 (SO14)

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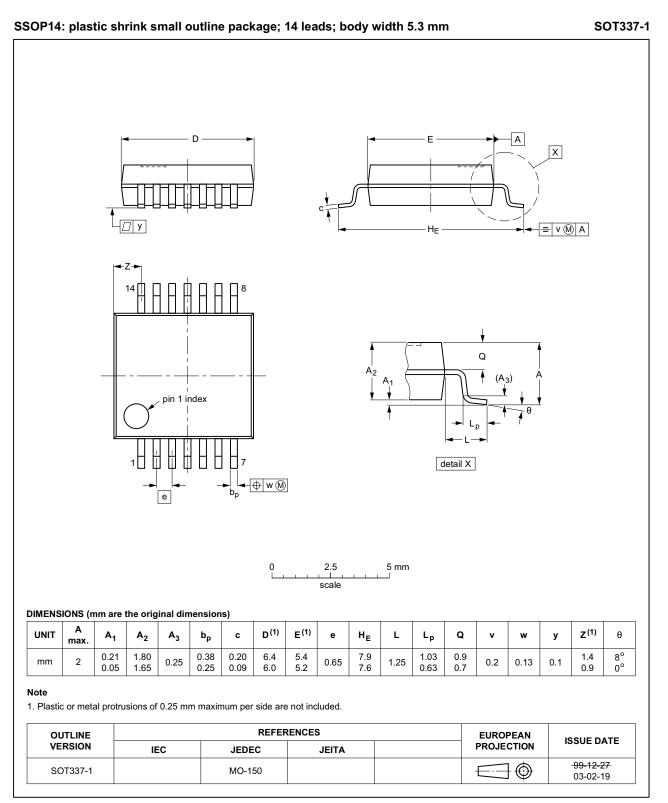


Fig 14. Package outline SOT337-1 (SSOP14)

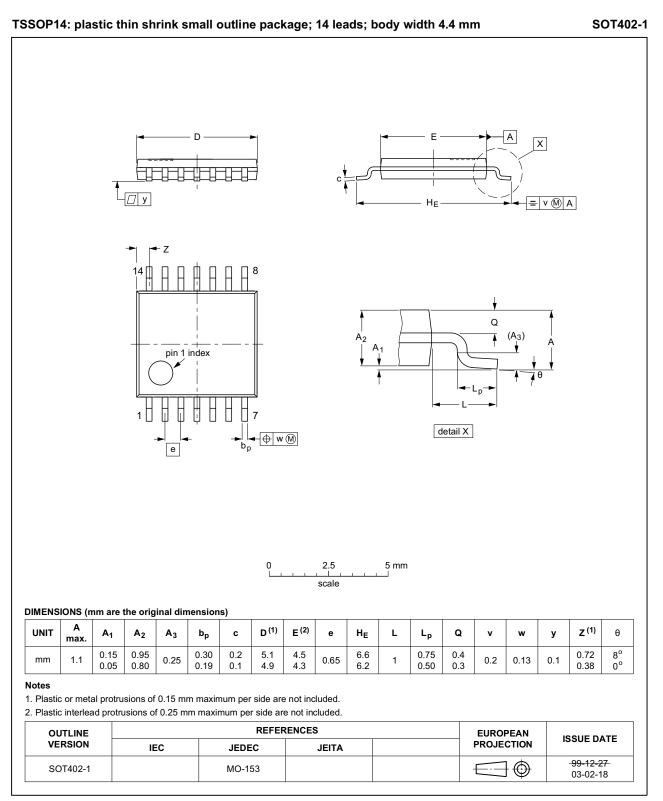
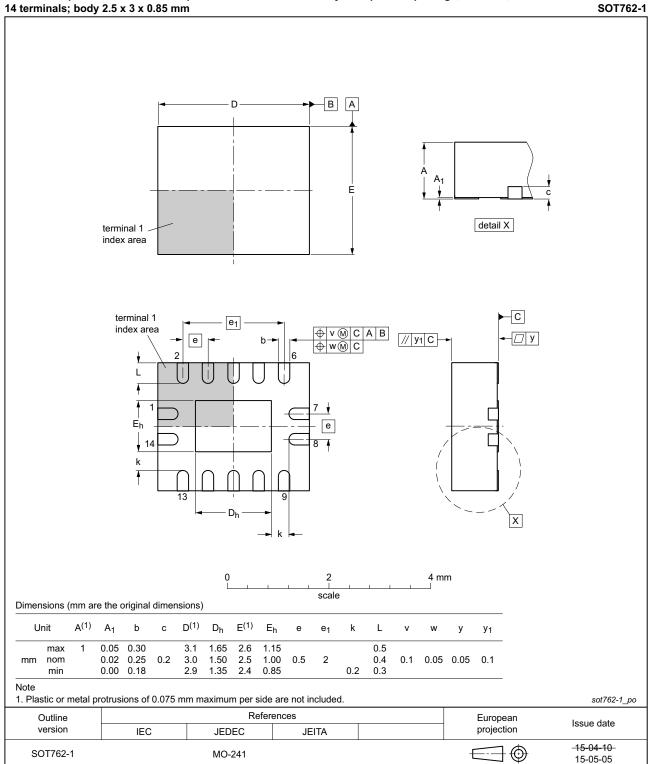


Fig 15. Package outline SOT402-1 (TSSOP14)

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DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads;

Fig 16. Package outline SOT762-1 (DHVQFN14)

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16. Abbreviations

Table 11. Abbreviations							
Acronym	Description						
CMOS	Complementary Metal Oxide Semiconductor						
DUT	Device Under Test						
ESD	ElectroStatic Discharge						
НВМ	Human Body Model						
MM	Machine Model						
TTL	Transistor-Transistor Logic						

17. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LV132 v.6	20151209	Product data sheet	-	74LV132 v.5
Modifications:	Type number	74LV132N (SOT27-1) remove	ed.	
74LV132 v.5	20090702	Product data sheet	-	74LV132 v.4
Modifications:	• <u>Table 6</u> : the co changed.	onditions for HIGH-level output	ut voltage and LOW-lev	vel output voltage have been
74LV132 v.4	20071112	Product data sheet	-	74LV132 v.3
74LV132 v.3	20040415	Product specification	-	74LV132 v.2
74LV132 v.2	19980428	Product specification	-	74LV132 v.1
74LV132 v.1	19970204	Product specification	-	-

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18.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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